Effect of Stress on Ferroelectricity of (Hf_{0.5}Zr_{0.5})O_2 Thin Films

Hiroshi Funakubo¹, ², Takahisa Shiraishi¹, Takao Shimizu², Tatsuhiko Yokouchi¹, Takahiro Oikawa¹, Hiroshi Uchida³

¹Department of Innovative and Engineered Materials, Tokyo Institute of Technology, 4259 Nagatsuta-cho, Midori-ku, Yokohama, 226-8502, Japan
Phone: +81-45-924-5446, E-mail: funakubo.h.aa@m.titech.ac.jp
²Materials Research Center for Element Strategy, Tokyo Institute of Technology, 4259 Nagatsuta-cho, Midori-ku, Yokohama, 226-8503 Japan
³Department of Materials and Life Sciences, Sophia University, Chiyoda-ku, Tokyo 102-8554, Japan

Abstract
Ferroelectricity was investigated for 17 and 55 -nm thick (Hf_{0.5}Zr_{0.5})O_2 thin films prepared by Pulsed MOCVD. Ferroelectricity strongly depended on the film thickness and the kinds of substrates. This suggests that the formation and the volume fraction of ferroelectric orthorhombic phase strongly depended on the stress applied to the films from the substrate.

1. Introduction
Ferroelectricity of thin films of HfO₂-based materials have been demonstrated by substituting various ions, such as Si, Y, Al, Zr, Gd, and Sr [1-3]. Most noticeable feature of these films compared to the previous ferroelectric films, such as Pb(Zr, Ti)O_3 and SrBi_2Ta_2O_9 films, is the appearance of ferroelectricity less than 10 nm in thickness even in polycrystalline film form. This feature is possible to realize not only low voltage operation of capacitor-type ferroelectric memories due to the very thin film thickness, but also ferroelectric transistor-type one due to the good compatibility of HfO₂-based insulators with CMOS. In addition, atomic layer deposition (ALD) technique is applicable for HfO₂-based ferroelectric films with three dimensional capacitors that are essential to realize high density capacitor-type ferroelectric memories.

Origin of the ferroelectricity is pointed out to be the non-centrosymmetric orthorhombic phases. This phase is non-equilibrium phase, but is pointed out to be stabilized in thin film form. Two stabilization factors are pointed out from the previous reports; one is the crystallite size and the other is the stress from the substrates. Crystalline size is systematically investigated by Hwan’s groups [4], but the stress effect from the substrate has been hardly reported. In the present study, we investigated the effect of the stress from the substrate by changing the kinds of substrates and film thickness.

2. Experimental Procedure
(Hf_{0.5}Zr_{0.5})O_2 thin films were prepared on the (111)Pt/SiO_2-coated substrates by pulsed metal organic chemical vapor deposition (MOCVD). Hf(NMe₂)(C₈H₁₇N₂) (Tosoh Corp.) and Zn(NMe₂)(C₈H₁₇N₂) (Tosoh Corp.) were supplied alternately as Hf and Zr source materials, respectively. The substrate temperature and chamber pressure during film growth were maintained at 350 °C and 4 Torr, respectively. The Hf/Zr ratio in the films was checked by the wavelength dispersive X-ray fluorescence. Details of the film deposition are already reported [5, 6]. Fused silica (SiO₂), (100)Si and (100)CaF₂ with the thermal expansion coefficient (α) of 0.5, 4.5, and 22 × 10⁻⁶/K, respectively, were used as substrates and (111)Pt and amorphous SiO₂ layers were prepared on these substrates by RF magnetron sputtering methods. Deposited (Hf_{0.5}Zr_{0.5})O_2 thin films were heat-treated at 700 °C for 10 min under atmospheric O₂ atmosphere.

Crystal structural characterization was performed by X-ray diffraction θ-2θ method. Electrical properties of the (Hf_{0.5}Zr_{0.5})O_2 films were investigated by the ferroelectric tester (Toyo Corp.) for P - E hysteresis measurement and by impedance analyzer (Agilent 4194A) for dielectric measurement. Low temperature measurement was performed using temperature-controlled prober station.

3. Results and Discussion
Figure 1(a) shows XRD θ-2θ patterns of 17 nm-thick films prepared on three kinds of substrates. Figure 1 (b) shows the enlarged one in the range of 2θ = 28° - 34°. Peak position of Pt (111) decreased with increasing α value of the substrates. This indicates that the out-of plane lattice spacing of Pt layer was increased with increasing α value of the substrates. This means that in-plane lattice spacing of Pt layer was decreased with increasing α value due to the thermal stress from the substrates.

Diffraction peaks from the films were also observed for all films shown in Fig. 1. However, the intensity ratio of orthorhombic (111)/tetragonal (101) to monoclinic (111) of the films on SiO₂ substrates was smaller than that of the films on Si substrate. On the other hand, orthorhombic (111)/tetragonal (101) was hardly observed for films on CaF₂ substrates.

Fig. 1 XRD θ-2θ patterns of 2θ=20 - 45 ° and 28 - 34 ° for 17 nm-thick films prepared on three kinds of substrates.
Figure 2 shows the room temperature polarization-electric filed ($P - E$) hysteresis loops measured at 10 kHz for the same films shown in Fig. 1. Hysteresis loops originating from the ferroelectricity were observed for all films. Remanent polarization ($P_r$) value decreased in the following order; films on SiO$_2$, Si and CaF$_2$ substrates. This order is in good agreement with decreasing peak position of Pt 111 in Fig. 1. $P_r$ value can be understood as the intensity ratio of the intensity ratio of orthorhombic 111/tetragonal 101 to monoclinic 111 as discussed in Fig. 1 because this ratio can be considered to be related to the volume fraction of orthorhombic phase.

Figure 3 show the room temperature polarization-electric filed ($P - E$) hysteresis loops for 55 nm-thick films. Hysteresis loops originating from the ferroelectricity was observed for films on Pt/SiO$_2$-coated SiO$_2$ substrate as shown in Fig. 3 (a). This is thickest (Hf$_{0.5}$Zr$_{0.5}$)O$_2$ film showing the ferroelectricity within our survey, although $P_r$ value of 55 nm-thick film was smaller than that of 17 nm thick films prepared on the same SiO$_2$ substrates. On the other hand, hysteresis loops were hardly observed for the films on Si and CaF$_2$ substrates as shown in Figs. 3 (b) and (c). This change of the ferroelectricity can be explained by the in-plane stress from the substrates; Stress applied from the substrates was relaxed by the increase of the film thickness of (Hf$_{0.5}$Zr$_{0.5}$)O$_2$ films.

These data show the impact of the stress from the substrates on the ferroelectricity of the (Hf$_{0.5}$Zr$_{0.5}$)O$_2$ thin films.

4. Conclusions
Ferroelectricity was investigated for 17 and 55 nm-thick (Hf$_{0.5}$Zr$_{0.5}$)O$_2$ thin films prepared on Pt/SiO$_2$-coated SiO$_2$, Si and CaF$_2$ substrates. Ferroelectricity was observed for 17 nm-thick films regardless of the kinds of substrates, while only films on SiO$_2$ substrate showed ferroelectricity for 55 nm-thick films. This can be understood by the volume fraction of orthorhombic phase. These results show the impact of the stress from the substrates on the ferroelectricity of the (Hf$_{0.5}$Zr$_{0.5}$)O$_2$ thin films.

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